

Vishay Siliconix

16 Ω , Low Parasitic Capacitance and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

DESCRIPTION

The DG411LE, DG412LE, and DG413LE are monolithic quad single-pole-single-throw analog switches. The DG411LE and DG412LE differ only in that they respond to opposite logic levels. The DG413LE has two normally open and two normally closed switches. It can be given various configurations, including four SPST, two SPDT, and one DPDT.

The DG411LE, DG412LE, and DG413LE offer low on resistance of 16 Ω , low parasitic capacitance of 15 pF switch on capacitance, and low charge injection over the signal swing range.

The DG411LE, DG412LE, and DG413LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with ± 3 V to ± 8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG411LE, DG412LE, and DG413LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

FEATURES

- 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply
- On-resistance R_{DS(on)}: 16 Ω
- Low parasitic capacitance: C_{D(ON)}: 15 pF C_{S(OFF)}: 5 pF
- Less than 8 pC charge injection over the full signal swing range
- Fast switching t_{ON}: 16 ns t_{OFF}: 9 ns
- TTL, CMOS compatible
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

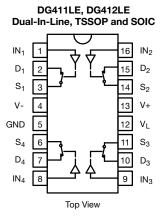
BENEFITS

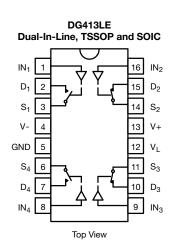
- Wide operation voltage range
- · Low signal errors and distortion
- · Fast switching time
- Minimized switching glitch

APPLICATIONS

- Automatic test equipment
- Data acquisition systems
- Meters and instruments
- Medical and healthcare systems
- Communication systems
- · Audio and video signal routing
- Relay replacement
- Battery powered systems
- Computer peripherals
- Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





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Document Number: 78091



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TRUTH TABLE	

LOGIC	DG411LE	DG412LE				
0	ON	OFF				
1	OFF	ON				
1 agia "0" < 0.9 V	•					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

TRUTH TABLE						
LOGIC	SW ₁ , SW ₄	SW ₂ , SW ₃				
0	OFF	ON				
1	ON	OFF				

Logic "0" \leq 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION								
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY				
		16-pin TSSOP	DG411LEDQ-GE3	Tube 360 units				
		10-pin 1330F	DG411LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG411LE	16-pin SOIC	DG411LEDY-GE3	Tube 500 units				
		10-pin 3010	DG411LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG411LEDJ-GE3	Tube 500 units				
	DG412LE	16-pin TSSOP	DG412LEDQ-GE3	Tube 360 units				
40.00 1 05.00			DG412LEDQ-T1-GE3	Tape and reel, 3000 units				
-40 °C to +85 °C Lead-free		16-pin SOIC	DG412LEDY-GE3	Tube 500 units				
			DG412LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG412LEDJ-GE3	Tube 500 units				
		16-pin TSSOP	DG413LEDQ-GE3	Tube 360 units				
		10-pin 1330F	DG413LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG413LE	16-pin SOIC	DG413LEDY-GE3	Tube 500 units				
		10-pin 3010	DG413LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG413LEDJ-GE3	Tube 500 units				

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	LIMIT	UNIT				
V+ to V-		-0.3 to +18				
GND to V-		18				
VL		(GND -0.3) to (V+) +0.3	V			
I _N ^a , V _S , V _D	-0.3 to (V+) +0.3 or 30 mA, whichever occurs first					
Continuous Current (Any terminal)	30					
Peak Current, S or D (Pulsed 1 ms, 10 % d	100	– mA				
Storago Tomporaturo	(DQ, DY suffix)		°C			
Storage Temperature	(AK suffix)	-65 to +150				
	16-pin TSSOP °					
Power Dissipation (Packages) ^b	16-pin SOIC ^d	650	mW			
	16-pin CerDIP ^e	900				
ESD Human Body Model (HBM); per ANSI	/ ESDA / JEDEC [®] JS-001	2500	V			
Latch Up Current, per JESD78D		400	mA			

Notes

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 75 °C

d. Derate 7.6 mW/°C above 75 °C

e. Derate 12 mW/°C above 75 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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DG411LE, DG412LE, DG413LE

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SPECIFICATIONS ^a (Single Su	pply 12 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^b	TYP. °	LIM	IFFIX IITS > +125 °C	LIN	IFFIX II TS D +85 °C	UNIT
		$V_{+} = 12 V, V_{-} = 0 V$ $V_{L} = 5 V, V_{IN} = 2.4 V, 0.8 V^{f}$			MIN. d	MAX. d	MIN. d		
Analog Switch	1	L		<u></u>		I	<u></u>	I	
Analog Signal Range ^e	VANALOG		Full	-	0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	V+ = 10.8 V, V- = 0 V I _S = 10 mA, V _D = 2/9 V	Room	16	-	26	-	26	Ω
OII-Resistance	- (-)	$I_{\rm S} = 10111 \text{A}, V_{\rm D} = 2/9 \text{ V}$	Full	-	-	40	-	35	
	I _{S(off)}		Room	-	-1	1	-1	1	
Switch Off Leakage Current	0(01)	V _D = 1/11 V, V _S = 11/1 V	Full	-	-15	15	-10	10	
5	I _{D(off)}		Room	-	-1	1	-1	1	nA
	D(OII)		Full	-	-15	15	-10	10	
Channel On Leakage	I _{D(on)}	$V_{\rm S} = V_{\rm D} = 11/1 \ {\rm V}$	Room	-	-1	1	-1	1	
Current	·D(01)		Full	-	-15	15	-10	10	
Digital Control									
Input Current, VIN Low	IIL	V _{IN} under test = 0.8 V	Full	0.01	-1.5	1.5	-1	1	μA
Input Current, VIN High	I _{IH}	V_{IN} under test = 2.4 V	Full		-1.5	1.5	-1	1	μΑ
Dynamic Characteristics									
	+		Room	16	-	50	-	50	ns
Turn-On Time	t _{ON}	$R_{l} = 300 \Omega, C_{l} = 35 pF,$	Full	-	-	70	-	60	
		$\overline{V}_{S} = 5 \text{ V}$, see figure 2	Room	9	-	30	-	30	
Turn-Off Time	t _{OFF}		Full	-	-	48	-	40	
Break-Before-Make Time Delay	t _D	DG413L only, V _S = 5 V, R _L = 300 Ω , CL = 35 pF	Room	5	-	-	-	-	
Charge Injection ^e	Q	V_g = 0 V, R_g = 0 Ω , C_L = 10 nF	Room	6.6	-	-	-	-	рС
Off-Isolation ^e	OIRR		Room	68.4	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	114	-	-	-	-	dB
Source Off Capacitance e	C _{S(off)}		Room	5	-	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	Room	6	-	-	-	-	pF
Channel-On Capacitance e	C _{D(on)}		Room	15	-	-	-	-	
Power Supplies				1		1	1		
			Room	0.02	-	1	-	1	
Positive Supply Current	I+		Full	-	-	7.5	-	5	1
		1	Room	-0.002	-1	-	-1	-	
Negative Supply Current	I-	N 97 57	Full	-	-7.5	-	-5	-	1
		$V_{IN} = 0 V \text{ or } 5 V$	Room	0.002	-	1	-	1	μA
Logic Supply Current	۱L		Full	-	-	7.5	-	5	1
	l .		Room	-0.002	-1	-	-1	-	
Ground Current	I _{GND}		Full	-	-7.5	-	-5	-	1

Notes

a. Refer to PROCESS OPTION FLOWCHART

b. Room = 25 °C, full = as determined by the operating temperature suffix

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

e. Guaranteed by design, not subject to production test

f. V_{IN} = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test

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SPECIFICATIONS ^a (Dual Supply ± 5 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^b	TYP. °	LIN	FFIX II TS +125 °C	LIN	JFFIX 11TS o +85 °C	UNIT
		V+ = 5 V, V- = -5 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^f			MIN. d	MAX. d	MIN. ^d	MAX. d	
Analog Switch	•						•		
Analog Signal Range ^e	V _{ANALOG}		Full	-	-5	5	-5	5	V
Drain-Source On-Resistance	R _{DS(on)}	V+ = 5 V, V- = -5 V, $I_S = 10 mA, V_D = \pm 3.5 V$	Room Full	18	-	30 42	-	30 37	Ω
			Room	-	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 5.5, V- = -5.5 V,	Full	-	-15	15	-10	10	
Leakage Current ^g		$V_{\rm P} = \pm 4.5 \text{ V}, V_{\rm S} = \pm 4.5 \text{ V}$	Room	-	-1	1	-1	1	
5	I _{D(off)}		Full	-	-15	15	-10	10	nA
Channel On		V+ = 5.5 V, V- = -5.5 V,	Room	-	-1	1	-1	1	
Leakage Current ^g	I _{D(on)}	$V_{\rm S} = V_{\rm D} = \pm 4.5 \text{ V}$	Full	_	-15	15	-10	10	
Digital Control							1		
Input Current, V _{IN} Low ^e	IIL	V _{IN} under test = 0.8 V	Full	0.05	-1.5	1.5	-1	1	
Input Current, V _{IN} High ^e	I _{IH}	V _{IN} under test = 2.4 V	Full	0.05	-1.5	1.5	-1	1	μA
Dynamic Characteristics					I		•	1	
T O T O			Room	17	-	50	-	50	
Turn-On Time ^e	t _{ON}	$R_L = 300 \Omega$, $C_L = 35 pF$,	Full	-	-	70	-	60	ns
		$V_{S} = \pm 3.5 V$, see figure 2	Room	12	-	35	-	35	
Turn-Off Time ^e	t _{OFF}		Full	-	-	50	-	40	115
Break-Before-Make Time Delay ^e	t _D	DG413L only, V _S = 3.5 V, R _L = 300 Ω, C _L = 35 pF	Room	5	-	-	-	-	
Charge Injection ^e	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	5.8	-	-	-	-	рС
Off Isolation ^e	OIRR		Room	68	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 $ Ω, $C_L = 5 $ pF, f = 1 MHz	Room	113	-	-	-	-	dB
Source Off Capacitance e	C _{S(off)}		Room	5	-	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	Room	6	-	-	-	-	pF
Channel On Capacitance ^e	C _{D(on)}		Room	14	-	-	-	-	
Power Supplies									
Positive Supply Current ^e	l+		Room	0.03	-	1	-	1	
T Ositive Supply Ourrent	IT		Full	-	-	7.5	-	5	
Negative Supply Current ^e	-		Room	-0.002	-1	-	-1	-	
Negative Supply Surrent	1	V _{IN} = 0 V or 5 V	Full	-	-7.5	-	-5	-	μA
Logic Supply Current ^e	ΙL		Room	0.002	-	1	-	1	- μΑ -
Logio cappi, cuiton	<u>د</u>		Full	-	-	7.5	-	5	
Ground Current ^e	I _{GND}		Room	-0.002	-1	-	-1	-	
	GND		Full	-	-7.5	-	-5	-	

Notes

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d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

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f. V_{IN} = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test

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SPECIFICATIONS ^a	SPECIFICATIONS ^a (Single Supply 5 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^b	IP. ^b TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 5 V, V- = 0 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^f			MIN. ^d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full	-	-	5	-	5	V
Drain-Source	R _{DS(on)}	V+ = 4.5 V,	Room	36	-	50	-	50	Ω
On-Resistance ^e	DS(on)	$I_{S} = 5 \text{ mA}, V_{D} = 1 \text{ V}, 3.5 \text{ V}$	Full	-	-	88	-	75	52
Dynamic Characteristics									
Turn-On Time ^e	t _{ON}		Room	27	-	50	-	50	
Tuni-On Time	LON	$R_L = 300 \Omega$, $C_L = 35 pF$,	Hot	-	-	90	-	60	ns
Turn-Off Time ^e	t _{OFF}	$V_{\rm S}$ = 3.5 V, see figure 2	Room	15	-	30	-	30	
	OFF		Hot	-	-	55	-	40	
Break-Before-Make Time Delay ^e	t _D	DG413L only, V_S = 3.5 V, R _L = 300 Ω , C _L = 35 pF	Room	11	-	-	-	-	
Charge Injection ^e	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	3.3	-	-	-	-	рС
Power Supplies									
Positive Supply Current ^e	l+		Room	0.02	-	1	-	1	
Positive Supply Current	1+		Hot	-	-	7.5	-	5	
Negative Supply Current e	I-		Room	-0.002	-1	-	-1	-	
Negative Supply Current	1-	Var = 0 V or 5 V	Hot	-	-7.5	-	-5	-	μA
Logic Supply Current ^e	IL	V _{IN} = 0 V or 5 V	Room	0.002	-	1	-	1	μΑ
	١Ľ		Hot	-	-	7.5	-	5	
Ground Current ^e	laura		Room	-0.002	-1	-	-1	-	
	I _{GND}		Hot	-	-7.5	-	-5	-	

Notes

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DG411LE, DG412LE, DG413LE

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SPECIFICATIONS ^a (Single Supply 3 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^b	TYP. °	ASUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 3 V, V- = 0 V V _L = 3 V, V _{IN} = 0.4 V, 2.0 V ^f			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch	•				•				
Analog Signal Range ^e	VANALOG		Full	-	0	3	0	3	V
Drain-Source On-Resistance	R _{DS(on)}	V+ = 2.7 V, V- = 0 V, I _S = 5 mA, V _D = 0.5, 2.2 V	Room Full	106 -	-	130 150	-	130 140	Ω
			Room	-	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 3.3. V- = 0 V.	Full	-	-15	15	-10	10	
Leakage Current ^g		$V_{\rm D} = 1, 2 \text{ V}, V_{\rm S} = 2, 1 \text{ V}$	Room	-	-1	1	-1	1	
	I _{D(off)}		Full	-	-15	15	-10	10	nA
Channel On		V+ = 3.3 V, V- = 0 V,	Room	-	-1	1	-1	1	
Leakage Current ^g	I _{D(on)}	$V_{\rm S} = V_{\rm D} = 1, 2 {\rm V}$	Full	-	-15	15	-10	10	
Digital Control									
Input Current, V _{IN} Low	۱ _{IL}	V_{IN} under test = 0.4 V	Full	0.005	-1.5	1.5	-1	1	μA
Input Current, V _{IN} High	I _{IH}	V _{IN} under test = 2.4 V	Full	0.005	-1.5	1.5	-1	1	μΛ
Dynamic Characteristics									
Turn-On Time	t _{ON}		Room	57	-	85	-	85	
	UN	$R_L = 300 \ \Omega, \ C_L = 35 \ pF,$	Full	-	-	150	-	110	
Turn-Off Time	t _{OFF}	$V_{S} = 1.5 V$, see figure 2	Room	25	-	60	-	60	ns
	•OFF		Full	-	-	100	-	85	
Break-Before-Make Time Delay	t _D	DG413L only, $V_S = 1.5 V$, R _L = 300 Ω , C _L = 35 pF	Room	24	-	-	-	-	
Charge Injection ^e	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	2	-	-	-	-	рС
Off Isolation ^e	OIRR		Room	68	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	107	-	-	-	-	dB
Source Off Capacitance ^e	C _{S(off)}		Room	6	-	-	-	-	
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	7	-	-	-	-	pF
Channel On Capacitance ^e	C _{D(on)}		Room	15	-	-	-	-	

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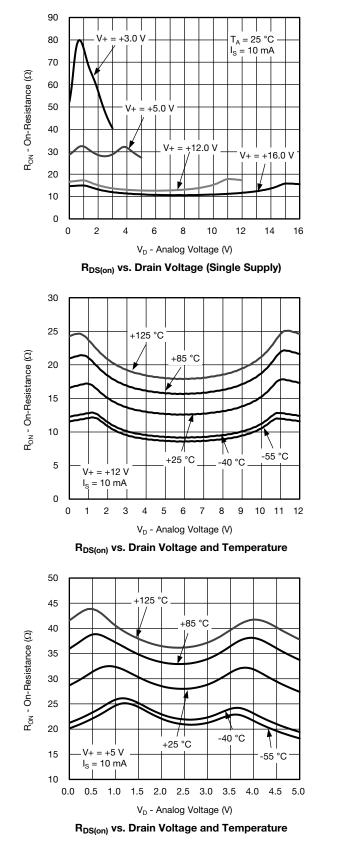
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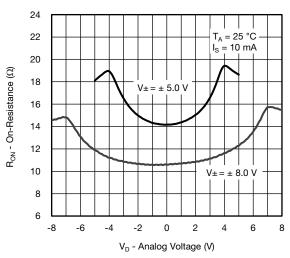
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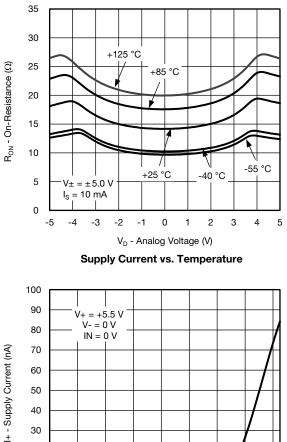
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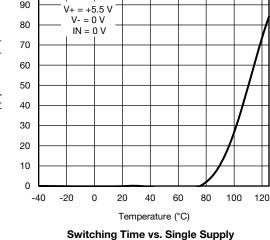
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





R_{DS(on)} vs. Drain Voltage and Temperature (Single Supply)





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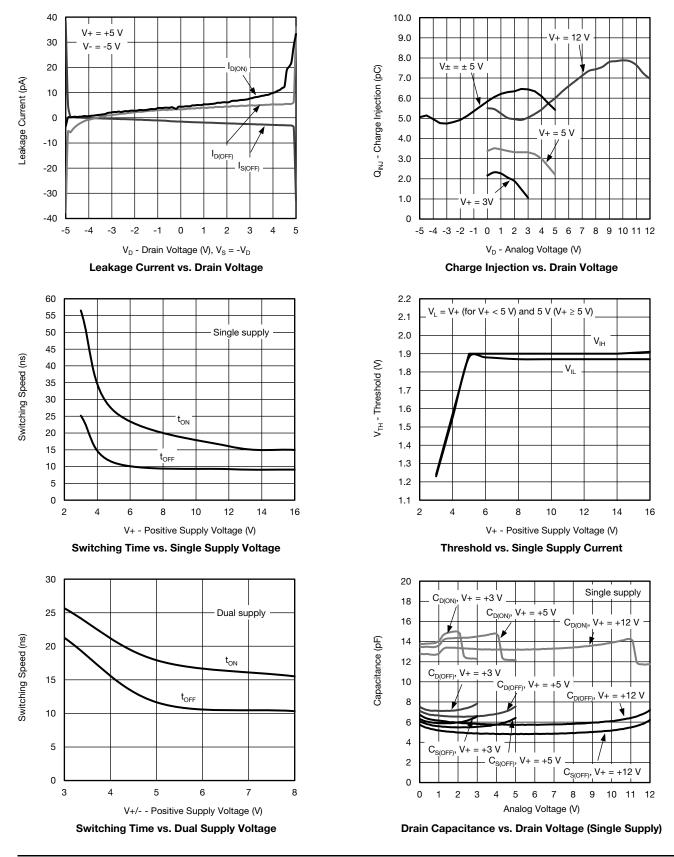
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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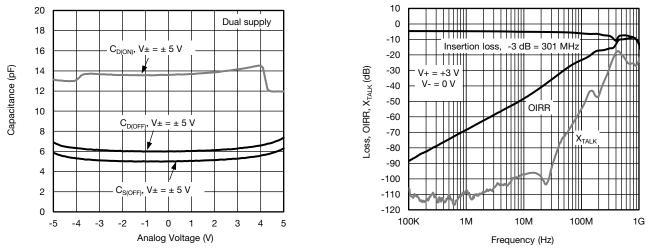
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Drain Capacitance vs. Drain Voltage (Dual Supply)

Insertion Loss, Off Isolation and Crosstalk vs. Frequency

SCHEMATIC DIAGRAM (Typical Channel)

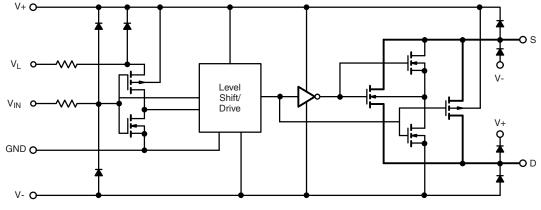
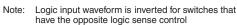
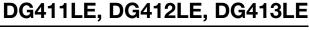


Fig. 1

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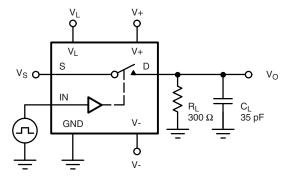
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TEST CIRCUITS

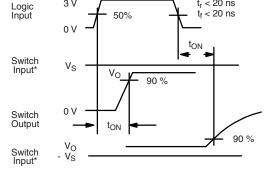
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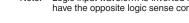


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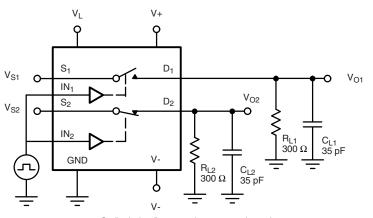
CL (includes fixture and stray capacitance)

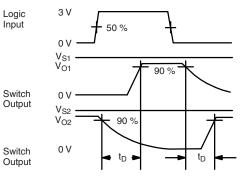






3 V

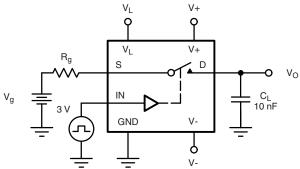


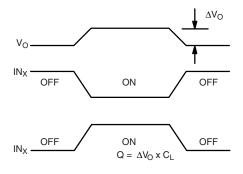


C_L (includes fixture and stray capacitance)

Fig. 3 - Break-Before-Make (DG413LE)

Fig. 2 - Switching Time





IN_X dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection

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t_r < 20 ns

t_f < 20 ns





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TEST CIRCUITS

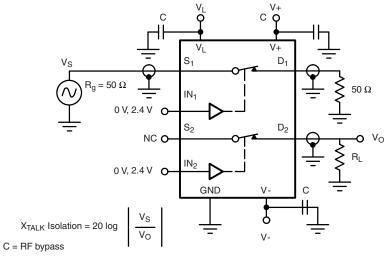
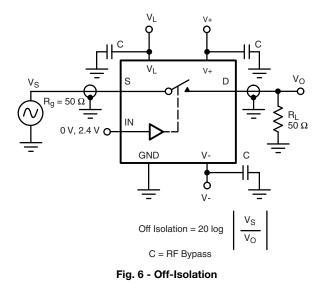


Fig. 5 - Crosstalk



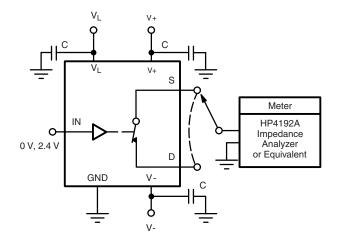


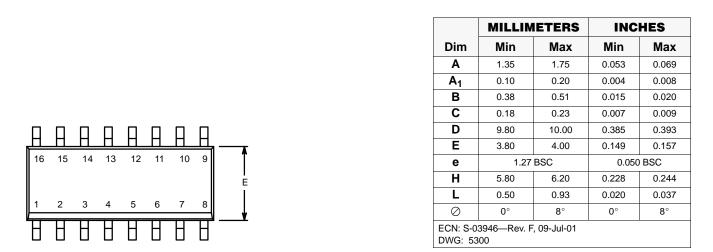
Fig. 7 - Source / Drain Capacitances

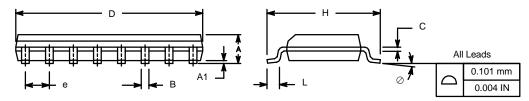
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?78091</u>.



SOIC (NARROW): 16-LEAD

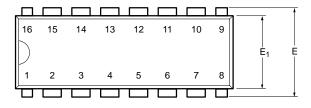
JEDEC Part Number: MS-012

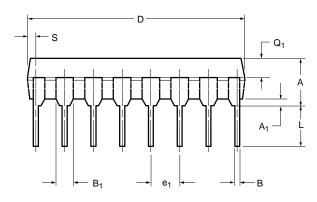


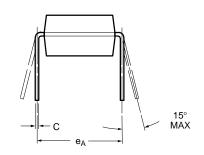




PDIP: 16-LEAD







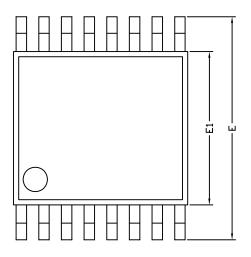
	MILLIN	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	3.81	5.08	0.150	0.200		
A ₁	0.38	1.27	0.015	0.050		
В	0.38	0.51	0.015	0.020		
B ₁	0.89	1.65	0.035	0.065		
С	0.20	0.30	0.008	0.012		
D	18.93	21.33	0.745	0.840		
E	7.62	8.26	0.300	0.325		
E ₁	5.59	7.11	0.220	0.280		
e ₁	2.29	2.79	0.090	0.110		
e _A	7.37	7.87	0.290	0.310		
L	2.79	3.81	0.110	0.150		
Q ₁	1.27	2.03	0.050	0.080		
S	0.38	1.52	.015	0.060		
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482						

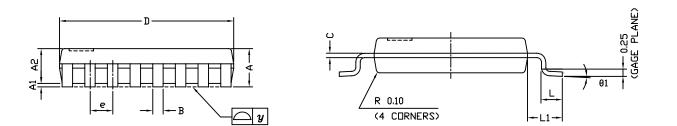


Package Information

Vishay Siliconix

TSSOP: 16-LEAD





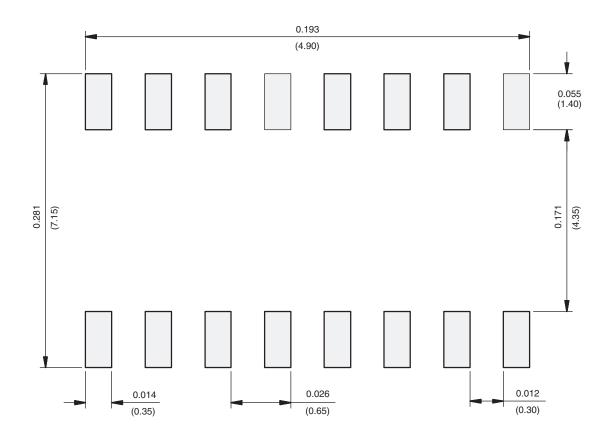
	C	DIMENSIONS IN MILLIMETERS					
Symbols	Min	Nom	Мах				
A	-	1.10	1.20				
A1	0.05	0.10	0.15				
A2	-	1.00	1.05				
В	0.22	0.28	0.38				
С	-	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	-	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06						



PAD Pattern

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RECOMMENDED MINIMUM PAD FOR TSSOP-16



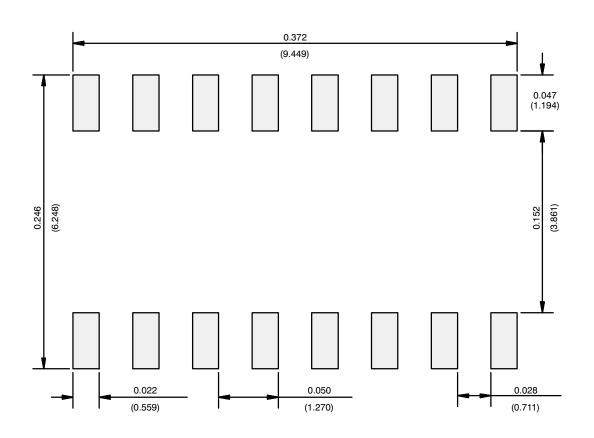
Recommended Minimum Pads Dimensions in inches (mm)

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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